SHI LING®

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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Symbol	Parameter	Test Conditions	Values	Unit
V_R	Maximum D.C. Reverse Voltage		1200	V
V_{RRM}	Maximum Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	T_C=100℃, Per Diode	200	A
		T_C=100℃, Per Moudle	400	A
$I_{F(RMS)}$	RMS Forward Current	T_C=100℃, Per Diode	260	A
I_{FSM}	Non-Repetitive Surge Forward Current	T_J=45℃, t=10ms, 50Hz, Sine	2200	A
		T_J=45℃, t=8.3ms, 60Hz, Sine	2400	A

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	V_R=1200V	--	--	40	uA
		V_R=1200V, T_J=125℃	--	--	200	uA
V_F	Forward Voltage	I_F=200A	--	2.0	--	V
		I_F=200A, T_J=125℃	--	1.8	--	V
t_{rr}	Reverse Recove ry Time	I_F=1A, V_R=30V, di_F/dt=-200A/μs	--	100	--	ns
t_{rr}	Reverse Recove ry Time	V_R=600V, I_F=200A	--	155	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-200A/μs, T_J=25℃	--	10	--	A
t_{rr}	Reverse Recovery Time	V_R=600V, I_F=200A	--	140	--	ns
I_{RRM}	Max. Reverse Recovery Curren	di_F/dt=-200A/μs, T_J=125℃	--	21	--	A

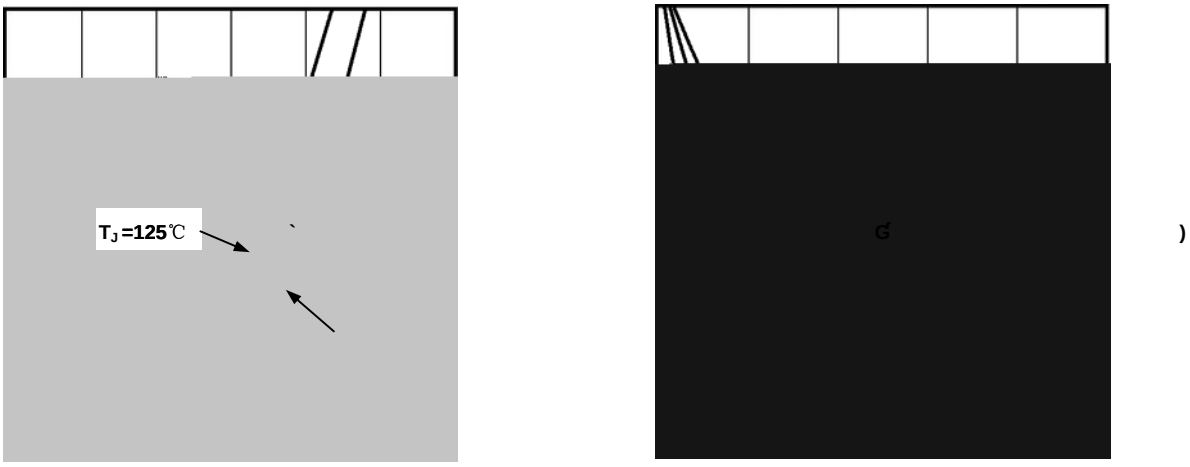


Figure1. Forward Voltage Drop vs Forward Current

